FOR LOW FREQUENCY POWER AMPLIFY APPLICATION SILICON NPN EPITAXIAL TYPE

DESCRIPTION

2SC3244 is a silicon NPN epitaxial type transistor designed with high collector dissipation, high voltage.

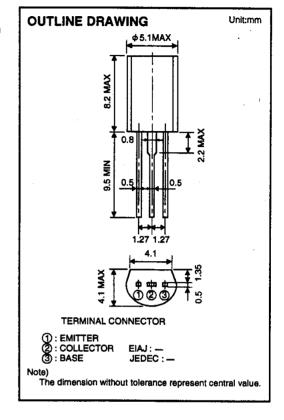
Complementary with 2SA1284.

FEATURE

- ●High voltage VcEo=100V
- ●High peak collector current icm=800mA
- ●High gain band width product. ft=130MHz (typ)
- ●High collector dissipation Pc=900mW

APPLICATION

Drive for 20 to 40W amplifier, relay drive, power supply application.



MAXIMUM RATINGS (Ta=25℃)

| Symbol | Parameter · | Ratings | Unit |
|--------|-------------------------------|-------------|------|
| Vсво | Collector to Base voltage | 100 | V |
| VEBO | Emitter to Base voltage | 5 | V |
| VCEO | Collector to Emitter voltage | 100 | V |
| Ісм | Peak collector current | 800 | mA |
| lc | Collector current | 500 | mA |
| Pc | Collector dissipation(Ta=25℃) | 900 | mW |
| Tj | Junction temperature | +150 | ార |
| Tstg | Storage temperature | -55 to +150 | Ψ |

ELECTRICAL CHARACTERISTICS (Ta=25℃)

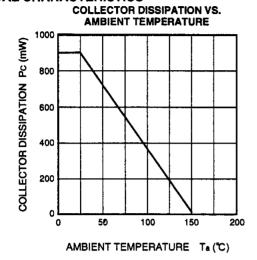
| Symbol | Parameter | Test conditions | | Limits | | |
|----------|------------------------------|---------------------|-----|-------------|-----|------|
| | | 1 43t COllettions | Min | Тур | Max | Unit |
| V(BR)CBO | C to B break down voltage | IC=10 μ A,IE=0 | 100 | 1 | | V |
| V(BR)EBO | E to B break down voltage | IE=10 μ A,IC=0 | 5 | i | | V |
| V(BR)CEO | C to E break down voltage | Ic=1mA,RBE=∞ | 100 | Ì | | V |
| Ісво | Collector cut off current | VcB=50V,IE=0 | | | 0.5 | μÂ |
| ІЕВО | Emitter cut off current | VEB=2V,IC=0 | | | 0.5 | μA |
| hfe + | DC forward current gain | VcE=10V,lc=10mA | 55 | | 300 | |
| VCE(sat) | C to E saturation voltage | lc=150mA,lb=15mA | | 0.15 | 0.5 | V |
| fr | Gain band width product | VcE=10V,IE=-10mA | | 130 | | MH≥ |
| Cob | Collector output capacitance | VcB=10V,IE=0,f=1MHz | | 6.5 | | pF |

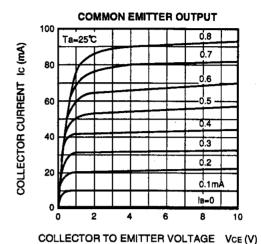
^{* :} It shows her classification in right table

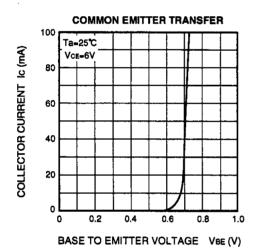
| item | C | D | E |
|------|-----------|-----------|------------|
| hfE | 55 to 110 | 90 to 180 | 150 to 300 |
| | | | |

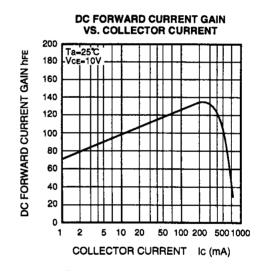
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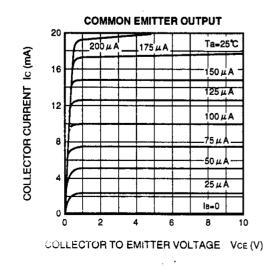
TYPICAL CHARACTERISTICS

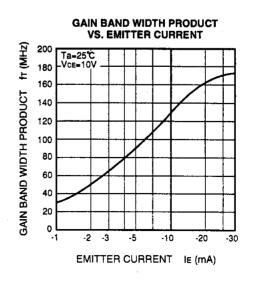




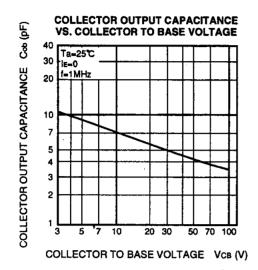








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